**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- · Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- · Enhanced power dissipation capability of 1390 mW

## 3. Applications

- · Relay driver
- · High-speed line driver
- · High-side load switch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-7	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -5.3 \text{ A}; T_j = 25 \text{ °C}$		-	28	34	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D
2	D	drain		
3	G	gate		G $\downarrow$ $\downarrow$ $\downarrow$
4	S	source	TSOP6 (SOT457)	
5	D	drain		
6	D	drain		S 047-00-250
				017aaa259

## **6. Ordering information**

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
PMN30XPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking code
PMN30XPE	3F

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-7	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-5.3	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-3.4	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-21	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	560	mW
			[1]	-	1.4	W
		T <sub>sp</sub> = 25 °C		-	6.25	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.4	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

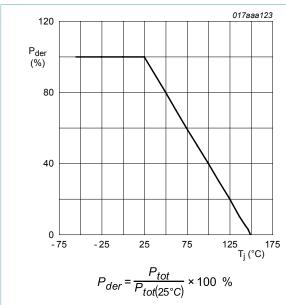


Fig. 1. Normalized total power dissipation as a function of junction temperature

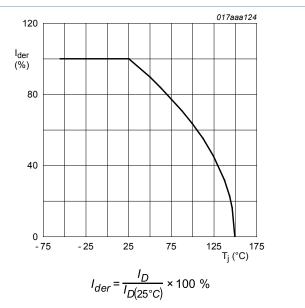


Fig. 2. Normalized continuous drain current as a function of junction temperature

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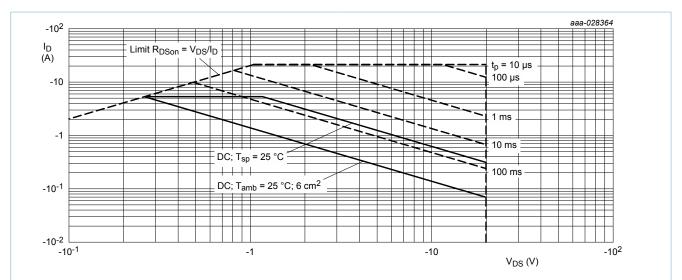


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

20 V, P-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		[1]	-	195	225	K/W
			[2]	-	78	90	K/W
		in free air, t ≤ 5 s	[2]	-	45	52	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

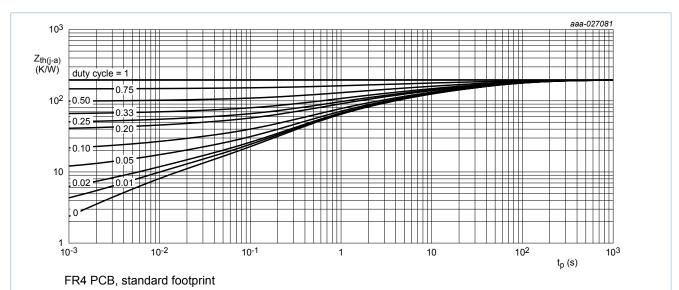


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

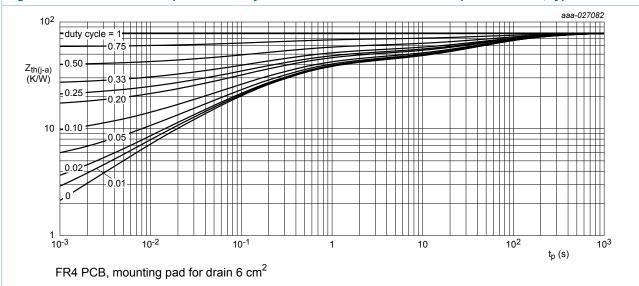


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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### 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			'		
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.75	-1	-1.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		$V_{GS}$ = -12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μΑ
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-5	μΑ
		V <sub>GS</sub> = 2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		$V_{GS} = -2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-100	nA
R <sub>DSon</sub> drain-source resistance	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -5.3 A; $T_j$ = 25 °C	-	28	34	mΩ
		V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -5.3 A; T <sub>j</sub> = 150 °C	-	40	49	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -4.1 A; $T_j$ = 25 °C	-	42	57	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -2 A; $T_{j}$ = 25 °C	-	13	-	S
$R_G$	gate resistance	f = 1 MHz	-	10.4	-	Ω
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -3 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	11	17	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	2	-	nC
$Q_{GD}$	gate-drain charge		-	2.5	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -10 \text{ V}$ ; f = 1 MHz; $V_{GS} = 0 \text{ V}$ ;	-	1465	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	193	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	133	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -10 \text{ V}; I_{D} = -3 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	27	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	62	-	ns
t <sub>f</sub>	fall time		-	28	-	ns
Source-dra	in diode		'		,	
V <sub>SD</sub>	source-drain voltage	$I_S$ = -1.4 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-0.7	-1.2	V

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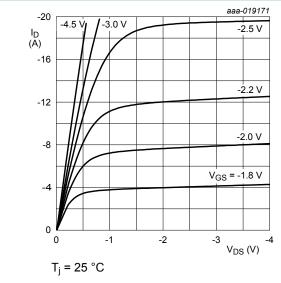


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

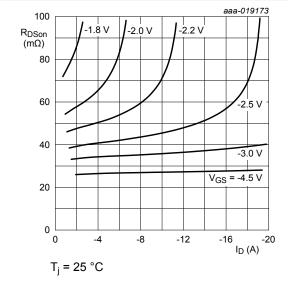


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

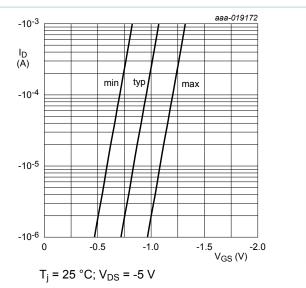


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

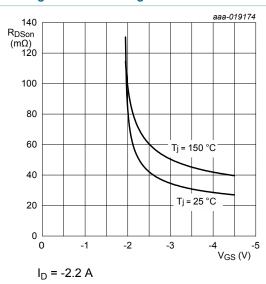


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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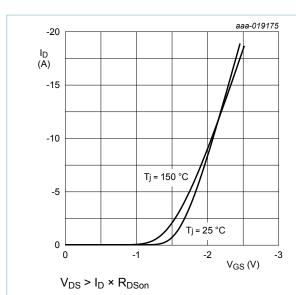


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

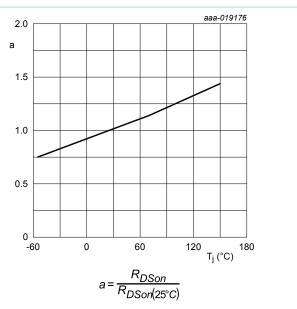


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

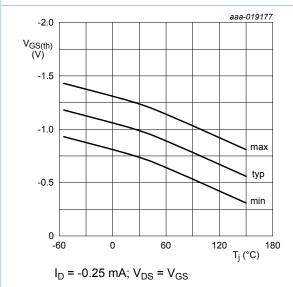


Fig. 12. Gate-source threshold voltage as a function of junction temperature

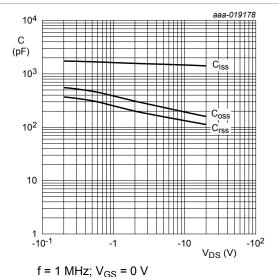


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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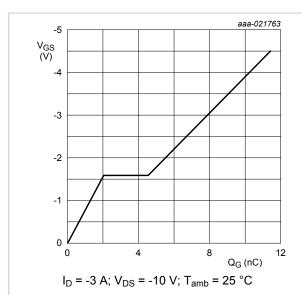


Fig. 14. Gate-source voltage as a function of gate charge; typical values

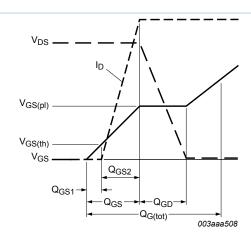


Fig. 15. Gate charge waveform definitions

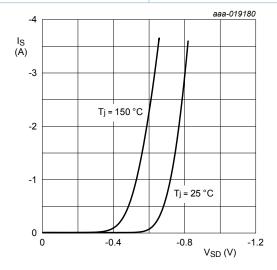
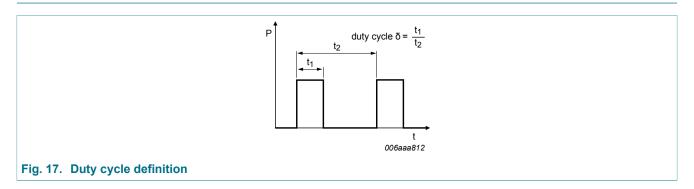


Fig. 16. Source current as a function of source-drain voltage; typical values

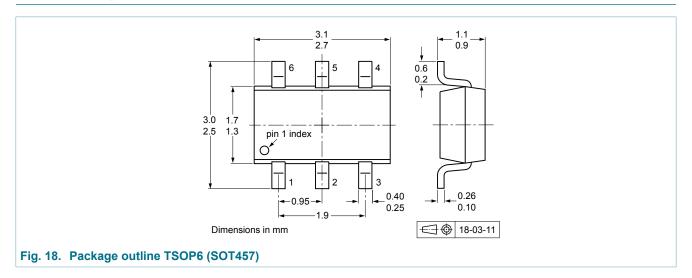
 $V_{GS} = 0 V$ 

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### 11. Test information

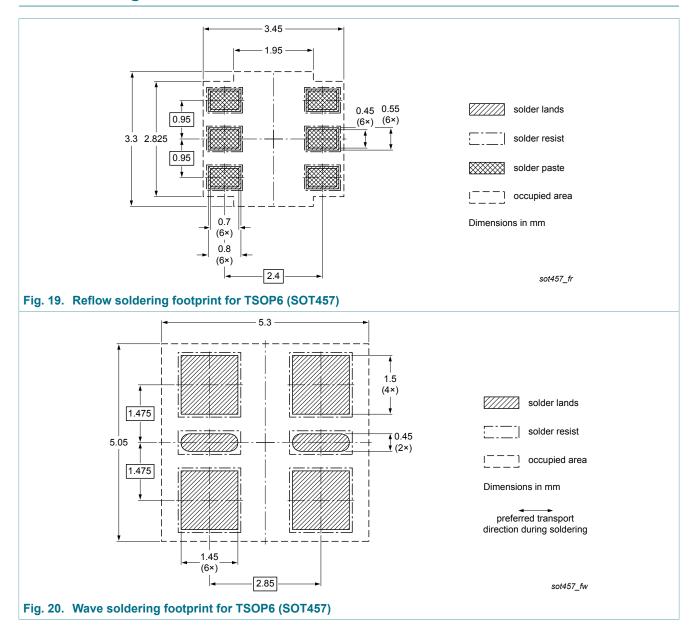


# 12. Package outline



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## 13. Soldering



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# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN30XPE v.1	20180416	Product data sheet	-	-

#### 20 V, P-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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